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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **MAKIYAMA, Kozo et al.**

Group Art Unit: 2826

Serial No.: 10/084,924

Examiner: **P. GREENE**

Filed: **March 1, 2002**

P.T.O. Confirmation No.: 7143

For: **SEMICONDUCTOR DEVICE WITH MUSHROOM ELECTRODE AND
MANUFACTURE METHOD THEREOF**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

April 2, 2003

Sir:

In response to the Office Action dated **January 2, 2003**, please amend the above-identified application as follows:

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IC 2800 MAIL ROOM

IN THE CLAIMS:

AMEND claim 1 to read as follows:

1. (Amended) A semiconductor device comprising:
- a semiconductor substrate having current input/output regions via which current flows;
 - a first insulating film formed on said semiconductor substrate and having a gate electrode opening; and
 - a mushroom gate electrode structure formed on said semiconductor substrate via the gate electrode opening, said mushroom gate electrode structure having a stem and a head formed on the stem, the stem having a limited size on said semiconductor substrate along a current direction and having a forward taper shape upwardly and monotonically increasing the size along the current

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